

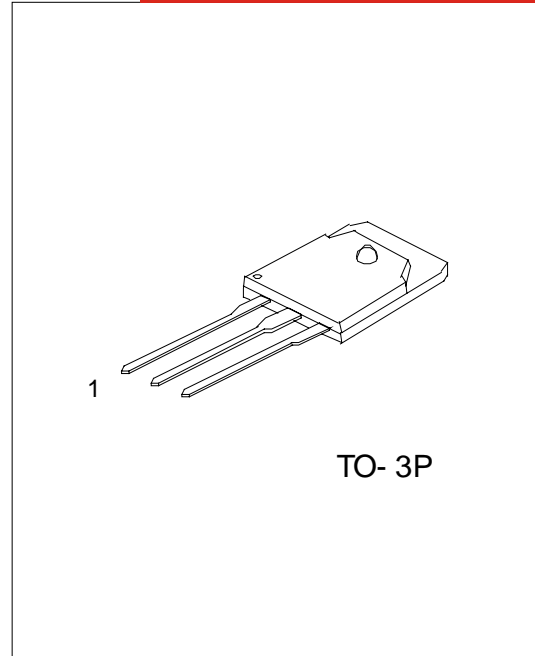


**NPN EPITAXIAL SILICON TRANSISTOR**  
**HIGH POWER AMPLIFIER APPLICATION**

勝特力材料 886-3-5753170  
勝特力电子(上海) 86-21-34970699  
勝特力电子(深圳) 86-755-83298787  
[Http://www.100y.com.tw](http://www.100y.com.tw)

**FEATURES**

- \*Recommended for 45~ 50W Audio Frequency Amplifier Output Stage.
- \*Complementary to 2SB688.



1: BASE 2:COLLECTOR 3: EMITTER

**ABSOLUTE MAXIMUM RATINGS** (Ta=25°C)

PARAMETER	SYMBOL	RATINGS	UNIT
Collector-Base Voltage	V <sub>CB0</sub>	120	V
Collector-Emitter Voltage	V <sub>CEO</sub>	120	V
Emitter-Base Voltage	V <sub>EBO</sub>	5	V
Collector Current	I <sub>c</sub>	10	A
Base Current	I <sub>b</sub>	1	A
Collector Power Dissipation (T <sub>c</sub> =25°C )	P <sub>c</sub>	80	W
Junction Temperature	T <sub>j</sub>	150	°C
Storage Temperature Range	T <sub>stg</sub>	- 55 ~ 150	°C

**ELECTRICAL CHARACTERISTICS** (Ta=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
Collector- Emitter Breakdown Voltage	V <sub>(BR)CEO</sub>	I <sub>c</sub> =50mA, b=0	120			V
Collector Cut- off Current	I <sub>CB0</sub>	V <sub>CB</sub> =120V, I <sub>E</sub> =0			10	μ A
Emitter Cut- off Current I <sub>E</sub>	I <sub>EBO</sub>	V <sub>EB</sub> =5V, I <sub>c</sub> =0			10	μ A
DC Current Gain	h <sub>FE</sub>	V <sub>CE</sub> =5V, I <sub>c</sub> =1A	55		160	
Collector- Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>c</sub> =6A, b=0.6A			2.0	V
Base- Emitter Voltage	V <sub>BE</sub>	V <sub>CE</sub> =5V, I <sub>c</sub> =5A			1.5	V
Transition Frequency	T <sub>f</sub>	V <sub>CE</sub> =5V, I <sub>c</sub> =1A		12		MHz
Collector Output Capacitance	C <sub>ob</sub>	V <sub>CB</sub> =10V, I <sub>E</sub> =0, f=1MHz		170		pF

**CLASSIFICATION OF h<sub>FE</sub>**

RANK	R	O
RANGE	55-110	80-160



# 2SD718

